

Plastic-Encapsulate Transistors

DUAL TRANSISTOR (PNP+PNP)

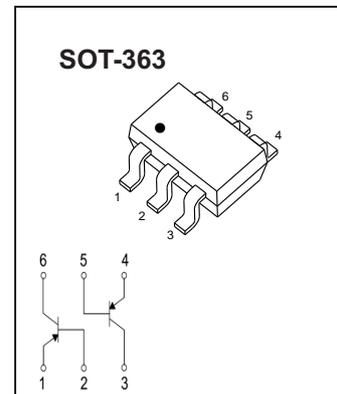
FEATURES

- Two transistors in one package
- Reduces number of components and board space
- No mutual interference between the transistors

MARKING: 3Kt

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CB0}	Collector- Base Voltage	-30	V
V_{CEO}	Collector-Emitter Voltage	-30	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-0.1	A
P_C	Collector Power Dissipation	0.2	W
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	625	$^\circ\text{C}/\text{W}$
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55-150	$^\circ\text{C}$



ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-10\mu\text{A}, I_E=0$	-30			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-10\text{mA}, I_B=0$	-30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-10\mu\text{A}, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-30\text{V}, I_E=0$			-15	nA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5\text{V}, I_C=0$			-100	nA
DC current gain	h_{FE}	$V_{CE}=-5\text{V}, I_C=-2\text{mA}$	110		600	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-10\text{mA}, I_B=-0.5\text{mA}$			-0.1	V
		$I_C=-100\text{mA}, I_B=-5\text{mA}^*$			-0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-10\text{mA}, I_B=-0.5\text{mA}$		0.7		V
Output Capacitance	C_{obo}	$V_{CB}=-10\text{V}, f=1\text{MHz}, I_E=0$			2.5	pF
Current Gain-Bandwidth Product	f_T	$V_{CE}=-5\text{V}, I_C=-10\text{mA}, f=100\text{MHz}$	100			MHz

*pulse test: $PW \leq 350\mu\text{s}$, $\delta \leq 2\%$.

